

Abstract of the Disclosure

A semiconductor memory device and a method for fabricating the same. Particularly, the semiconductor memory
5 device includes at least two capacitors to decrease the thickness of an insulation layer and increase the size of each capacitor, wherein the thickness of the insulation layer and the size of the capacitor are factors for increasing parasitic capacitance and leakage currents. Also, the two capacitors
10 are arranged diagonally, thereby widening the width of each capacitor formed. Furthermore, in forming double capacitors according to the preferred embodiment of the present invention, an additional reticle is not required to form the contact holes for each capacitor due to their inverted
15 disposition relationship.